

#### **GENERAL DESCRIPTION**

The SGM41522, SGM41522A and SGM41522B are compact switch standalone battery chargers for single-cell Li-lon or Li-polymer battery. They are featured with resistor programmable maximum charge current, ordering selections of preset end of charge current and pre-charge current and floating time out. The SGM41522, SGM41522A and SGM41522B also have other safety features, such as over-voltage and over-current protections, fold-back retaining, input under-voltage lockout, battery temperature monitoring and thermal shutdown. These features ensure safe and reliable operation, ease of design and a comfortable user experience.

The SGM41522, SGM41522A and SGM41522B are available in a Green TDFN-2×3-8BL package. They operate over an ambient temperature range of -40°C to +85°C.

#### **APPLICATIONS**

Portable Audio Speaker Mobile Phone Wearables EPOS

#### **FEATURES**

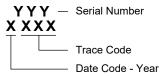
- Maximum 2.5A Charging for 4.1V to 4.45V Battery
- 1.33MHz Switch Frequency
- Up to 95.4% Charge Efficiency
- 92.8% Charge Efficiency at 1.5A from 5V Input
- 90.1% Charge Efficiency at 1.5A from 9V Input
- Charging Voltage and Current Programmable
- CC/CV Interface for Charge Current and Battery Voltage Settings
- 4.2V Input Voltage Regulation
- 4.2V to 12V Operating Input Voltage Range
- Up to 18V Sustainable Voltage
- 13.5V Over-Voltage Protection with 100ns Turn-Off Timer
- Output Voltage Fold-Back Retaining
- JEITA Guideline Compliance
  - T2 Threshold 10°C (SGM41522/SGM41522B)
  - T2 Threshold 15°C (SGM41522A)
  - Charge Prohibited when > T3 (SGM41522B)
- -40°C to +85°C Operating Temperature Range
- Available in a Green TDFN-2×3-8BL Package

#### PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM41522	TDFN-2×3-8BL	-40°C to +85°C	SGM41522YTDC8G/TR	RE1 XXXX	Tape and Reel, 3000
SGM41522A	TDFN-2×3-8BL	-40°C to +85°C	SGM41522AYTDC8G/TR	SHG XXXX	Tape and Reel, 3000
SGM41522B	TDFN-2×3-8BL	-40°C to +85°C	SGM41522BYTDC8G/TR	073 XXXX	Tape and Reel, 3000

#### MARKING INFORMATION

NOTE: XXXX = Date Code and Trace Code.



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

#### **ABSOLUTE MAXIMUM RATINGS**

Voltage Range (with Respect to GND)	
VBUS (Converter Not Switching)	2V to 18V
BTST (Converter Not Switching)	0.3V to 18V
SW, BAT	2V to 14V
BTST to SW	0.3V to 6V
REGN, TS (Converter Not Switching)	0.3V to 6V
CC, CV	0.3V to 6V
Package Thermal Resistance	
TDFN-2×3-8BL, $\theta_{JA}$	55°C/W
Junction Temperature	
Storage Temperature Range	65°C to +150°C
Lead Temperature (Soldering, 10s)	+260°C
ESD Susceptibility	
HBM	2000V
CDM	1000V

#### RECOMMENDED OPERATING CONDITIONS

Input Voltage Range, V <sub>VBUS</sub>	4.2V to 12V
Input Current (VBUS), I <sub>IN</sub>	2.5A (MAX)
Output Current (SW), I <sub>SWOP</sub>	2.5A (MAX)
Battery Voltage, VBATOP	4.45V (MAX)
Fast Charge Current, I <sub>CHGOP</sub>	2.5A (MAX)
Ambient Temperature Range	40°C to +85°C
Junction Temperature Range	40°C to +125°C

#### **OVERSTRESS CAUTION**

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

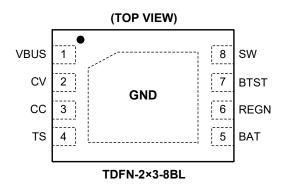
#### **ESD SENSITIVITY CAUTION**

This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

#### **DISCLAIMER**

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

### **PIN CONFIGURATION**



#### PIN DESCRIPTION

PIN	NAME	TYPE (1)	FUNCTION
1	VBUS	Р	Charger Input and Voltage Sense. Connect a 10µF ceramic capacitor from VBUS pin to GND close to device.
2	CV	AI	Charge Voltage Programming Input Pin. Connect a resistor between this pin and GND, for feeding different voltages to select 6 different charge voltages.
3	CC	Al	Charge Current Programming and Charging Inhibition Input Pin. Connect a resistor between this pin and GND for programming the constant charge current by $I_{CHGREG} = K \cdot V_{REF}/R_{CC}$ . Pull up this pin to a voltage higher than $V_{CC\_H}$ (1.4V) to stop charging.
4	TS	AI	Temperature Sense Input Pin. Connect to the battery NTC thermistor that is grounded on the other side. To program operating temperature window, it can be biased by a resistor divider between REGN and GND. Charge suspends if TS voltage goes out of the programmed range. It is recommended to use a 103AT-2 type thermistor. If NTC or TS pin function is not needed, use a $10k\Omega/10k\Omega$ pair for the resistor divider.
5	BAT	Р	Battery Positive Terminal Pin. Use a 22µF capacitor between BAT and GND pins close to the device.
6	REGN	Р	LDO Output that Powers LSFET Driver and Internal Circuits. Internally, the REGN pin is connected to the anode of the bootstrap diode. Place a $1\mu F$ (10V rating) ceramic capacitor between REGN pin and GND. It is recommended to place the capacitor close to the REGN pin.
7	BTST	Р	High-side Driver Positive Supply. It is internally connected to the bootstrap diode cathode. Use a 10nF ceramic capacitor from SW pin to BTST pin.
8	SW	Р	Switching Node Output. Connect SW pin to the output inductor. Connect the 10nF bootstrap capacitor from SW pin to BTST pin.
Exposed Pad	GND	Р	Thermal Pad and Ground Reference. It is the ground reference for the device and also the thermal pad to conduct heat from the device (not suitable for high current return). Tie externally to the PCB ground plane (GND). Thermal vias under the pad are needed to conduct the heat to the PCB ground planes.

#### NOTE:

1. Al = Analog Input, AO = Analog Output, AIO = Analog Input and Output, DI = Digital Input, DO = Digital Output, DIO = Digital Input and Output, P = Power.

### **ELECTRICAL CHARACTERISTICS**

 $(V_{VBUS\_UVLOZ} < V_{VBUS\_OV} \text{ and } V_{VBUS} > V_{BAT} + V_{SLEEP}, T_J = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ typical values are at } T_J = +25^{\circ}\text{C}, \text{ unless otherwise noted.})$ 

PARAMETER	SYMBOL	Co	ONDITIONS	MIN	TYP	MAX	UNITS	
Quiescent Currents								
		V <sub>BAT</sub> = 4.5V, V <sub>VBUS</sub> <	V <sub>VBUS-UVLOZ</sub> or no VBUS		0.1	1.0		
Battery Discharge Current (BAT)	I <sub>BAT</sub>	V <sub>BAT</sub> = 4.5V, V <sub>VBUS</sub> =	5V, fold-back mode		4.5	7.0	μA	
		$V_{VBUS} = 5V$ , $V_{VBUS} > V_{BAT}$ , converter not switching			1.4			
Input Supply Current (VBUS)		V <sub>VBUS</sub> = 12V, V <sub>VBUS</sub> >	V <sub>BAT</sub> , converter not switching		1.7	2.2	mA	
піриї Зирріу Сипені (УВОЗ)	I <sub>VBUS</sub>	V <sub>BAT</sub> = 3.8V, V <sub>VBUS</sub> > converter switching	$V_{BAT}$ , $V_{VBUS} > V_{VBUS\_UVLOZ}$ ,		8		IIIA	
BAT Pin and VBUS Pin Power-Up	I	l				I		
VBUS Operating Range	$V_{VBUS\_OP}$	V <sub>VBUS</sub> rising		4.2		13.2	V	
VBUS for Device Active, No Battery Sense VBUS Pin Voltage	V <sub>VBUS_UVLOZ</sub>	$V_{VBUS}$ rising, $T_J = +2$	5°C		3.32	3.46	V	
Device Active Hysteresis	V <sub>VBUS_UVLOZ_HYS</sub>	V <sub>VBUS</sub> falling from ab	ove V <sub>VBUS_UVLOZ</sub>		70		mV	
Sleep Mode Falling Threshold	V <sub>SLEEP</sub>	$V_{VBUS}$ - $V_{BAT}$ , $V_{VBUSMI}$ $T_J$ = +25°C	$_{N} \le V_{BAT} \le V_{REGN}, V_{VBUS}$ falling,		80	165	mV	
Sleep Mode Rising Threshold	V <sub>SLEEPZ</sub>	$V_{VBUS}$ - $V_{BAT}$ , $V_{VBUSMI}$ $T_J = +25^{\circ}C$	$_{N} \le V_{BAT} \le V_{REGN}, V_{VBUS}$ rising,	100	175	260	mV	
VBUS 13V Over-Voltage Rising Threshold	V <sub>VBUS_OV_RISE</sub>	V <sub>VBUS</sub> rising		12.78	13.4	13.90	V	
VBUS 13V Over-Voltage Hysteresis	$V_{VBUS\_OV\_HYS}$	V <sub>VBUS</sub> falling			355		mV	
Bad Adapter Detection Falling Threshold	V <sub>VBUSMIN</sub>	V <sub>VBUS</sub> falling	V <sub>VBUS</sub> falling		3.70	3.89	V	
Bad Adapter Detection Hysteresis	V <sub>VBUSMIN_HYS</sub>				250		mV	
Bad Adapter Detection Current Source	I <sub>BAD_SRC</sub>	Sink current from VBUS to GND, T <sub>J</sub> = +25°C		17	24	30	mA	
Power Path Management								
Total High-side MOSFET On-Resistance - (Q1 + Q2)	R <sub>ON_HSFET</sub>	V <sub>REGN</sub> = 5V			150		mΩ	
Low-side Switching MOSFET On-Resistance - Q3	R <sub>ON_LSFET</sub>	V <sub>REGN</sub> = 5V			110		mΩ	
Battery Charger								
Charge Voltage Program Range	V <sub>BATREG_RANGE</sub>	T <sub>J</sub> = +25°C		4.10		4.45	V	
Charge Voltage Step	V <sub>BATREG_STEP</sub>				50		mV	
		$R_{CV} = 0\Omega$ or floating	T <sub>J</sub> = +25°C	4.188	4.200	4.212		
Initial Charge Valtage Catting	V	(4.2V)	T <sub>J</sub> = -40°C to +85°C	4.171	4.200	4.229	,.	
Initial Charge Voltage Setting	$V_{BATREG}$	$R_{CV} = 22.1k\Omega$	T <sub>J</sub> = +25°C	4.334	4.347	4.361	V	
		(4.35V)	T <sub>J</sub> = -40°C to +85°C	4.317	4.347	4.378	]	
Charge Current Regulation Range	I <sub>CHGREG_RANGE</sub>			0		2500	mA	
			-0.5454 T - :05°0	0.475	0.510	0.550	Α	
			$I_{CHGREG} = 0.515A, T_{J} = +25^{\circ}C$	-6.7		8.0	%	
Initial Charge Current Begulation			- 4 2254 T - 105°C	1.19	1.23	1.28	Α	
Initial Charge Current Regulation Setting	I <sub>CHGREG</sub>	$V_{BAT} = 3.8V$	$I_{CHGREG} = 1.235A, T_J = +25^{\circ}C$	-3.6		3.5	%	
			I <sub>CHGREG</sub> = 1.535A, T <sub>J</sub> = +25°C	1.480	1.535	1.580	Α	
			I <sub>CHGREG</sub> = 1.535A, T <sub>J</sub> = -40°C to +85°C	1.455	1.535	1.605	Α	
Initial Pre-Charge Current		V <sub>BAT</sub> = 2.6V,	I <sub>CHGREG</sub> = 0.515A	31	55	88	_	
Regulation Setting	I <sub>PRECHG</sub>	$T_J$ = +25°C, $I_{PRECHG}$ is 10% of $I_{CHGREG}$	I <sub>CHGREG</sub> = 1.235A	101	130	163	mA	
	l	01101120	I					

## **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{VBUS\_UVLOZ} < V_{VBUS\_OV} \text{ and } V_{VBUS} > V_{BAT} + V_{SLEEP}, T_J = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ typical values are at } T_J = +25^{\circ}\text{C}, \text{ unless otherwise noted.})$ 

PARAMETER	SYMBOL	CONDITION	NS	MIN	TYP	MAX	UNITS
Battery Charger							
Battery LOW Falling Threshold	V <sub>BATLOW_FALL</sub>	I <sub>CHGREG</sub> = 600mA, T <sub>J</sub> = +25°C		2.68	2.79	2.91	V
Battery LOW Rising Threshold	V <sub>BATLOW_RISE</sub>	Pre-charge to fast charge			3.10		V
Initial Termination Current		V <sub>BAT</sub> = 4.1V, T <sub>J</sub> = +25°C,	$I_{CHGREG} = 0.515A$	21.5	51	80.5	mA
Regulation Setting	I <sub>TERM</sub>	I <sub>TERM</sub> is 10% of I <sub>CHGREG</sub>	I <sub>CHGREG</sub> = 1.235A	92.5	123	154	IIIA
Initial Battery Short Voltage	$V_{SHORT}$	$V_{BAT}$ falling, $T_J = +25^{\circ}C$		2.02	2.05	2.09	V
Illitial Battery Short Voltage	$V_{SHORTZ}$	V <sub>BAT</sub> rising, T <sub>J</sub> = +25°C		2.15	2.19	2.22	V
Initial Battery Short Current	I <sub>SHORT</sub>	V <sub>BAT</sub> < V <sub>SHORTZ</sub>		30	33.5	38	mA
Fold-Back Mode Threshold below V <sub>BATREG</sub>	V <sub>FOLDBACK</sub>	V <sub>BAT</sub> falling			90		mV
Recharge Threshold below V <sub>BATREG</sub>	$V_{RECHG}$	$V_{BAT}$ falling, $T_J = +25^{\circ}C$		85	140	190	mV
Charge Current Amplification Ratio	K				10300		
Constant Current Control Reference Voltage	$V_{REF}$				1		V
Input Voltage Regulation							
Input Voltage Regulation Limit	$V_{INDPM}$	LVDPM version			4.16		V
BAT Pin Over-Voltage Protection							
Dettem Over Veltere Threehold	V <sub>BATOVP_RISE</sub>	As percentage of V <sub>BATREG</sub> ,	V <sub>BAT</sub> rising	103	104.5	106	- %
Battery Over-Voltage Threshold	$V_{BATOVP\_FALL}$	T <sub>J</sub> = +25°C	V <sub>BAT</sub> falling	101	102.5	104	/0
Thermal Regulation and Thermal S	hutdown						
Junction Temperature Regulation Threshold	T <sub>JUNCTION_REG</sub>	Temperature increasing			110		°C
Thermal Shutdown Rising Temperature	T <sub>SHUT</sub>	Temperature increasing			150		°C
Thermal Shutdown Hysteresis	T <sub>SHUT_HYS</sub>				10		°C
JEITA Thermistor Comparator							
T1 (0°C) Threshold Voltage on TS Pin	V <sub>T1</sub>	Charger suspends if temperat (T < T1), as percentage to V <sub>RI</sub>			73.2		%
V <sub>⊺1</sub> Falling	• 11	As percentage of V <sub>REGN</sub>			71.3		%
T2 (10°C) Threshold Voltage on TS Pin	$V_{T2}$	Charge back to I <sub>CHGREG</sub> /10 and V <sub>BATREG</sub> - 100mV if T1 < T < T2, as percentage of V <sub>REGN</sub> (SGM41522/SGM41522B)			68.1		%
V <sub>T2</sub> Falling		As percentage of V <sub>REGN</sub> (SGM	41522/SGM41522B)		66.6		%
T2 (15°C) Threshold Voltage on TS Pin	$V_{T2}$	Charge back to I <sub>CHGREG</sub> /10 and V <sub>BATREG</sub> - 100mV if T1 < T< T2, as percentage of V <sub>REGN</sub> (SGM41522A)			65.1		%
V <sub>T2</sub> Falling	V 12	As percentage of V <sub>REGN</sub> (SGM41522A)			63.3		%
V <sub>T3</sub> Rising		As percentage of V <sub>REGN</sub>			46.0		%
T3 (45°C) Threshold Voltage on TS Pin	$V_{T3}$	Charge back to I <sub>CHGREG</sub> /10 and V <sub>BATREG</sub> - 100mV if T3 < T < T4, as percentage to V <sub>REGN</sub>			44.2		%
V <sub>T4</sub> Rising		As percentage of V <sub>REGN</sub>			35.8		%
T4 (60°C) Threshold Voltage on TS Pin	$V_{T4}$	Charge suspended if T > T4, as percentage of V <sub>REGN</sub>			34.6		%

## **ELECTRICAL CHARACTERISTICS (continued)**

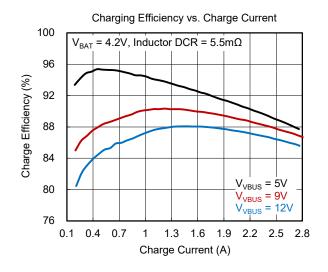
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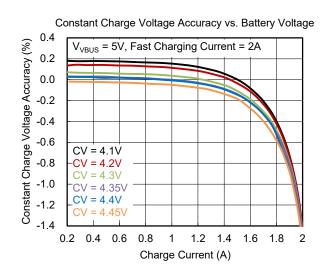
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
Charge Over-Current Comparator	Charge Over-Current Comparator (Cycle-by-Cycle)						
HSFET Cycle-by-Cycle Over-Current Threshold	I <sub>HSFET_OCP</sub>			4		Α	
Charge Under-Current Comparate	or (Cycle-by-Cyc	ele)					
LSFET Under-Current Falling Threshold	V <sub>LSFET_UCP</sub>	From sync mode to non-sync mode		100		mA	
PWM							
PWM Switching Frequency	f <sub>SW</sub>	Oscillator frequency, Buck mode, T <sub>J</sub> = +25°C	1.20	1.33	1.45	MHz	
Maximum PWM Duty Cycle	D <sub>MAX</sub>			98		%	
REGN LDO							
DECN I DO Output Voltage	\/	V <sub>VBUS</sub> = 9V, I <sub>REGN</sub> = 40mA	4.70	4.90	5.10	V	
REGN LDO Output Voltage	$V_{REGN}$	V <sub>VBUS</sub> = 5V, I <sub>REGN</sub> = 20mA	4.79	4.86	4.92	V	
REGN LDO Maximum Output Current	I <sub>REGN_MAX</sub>	V <sub>VBUS</sub> = 5V	56	68	80	mA	

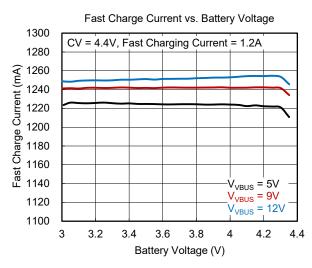
#### **TIMING REQUIREMENTS**

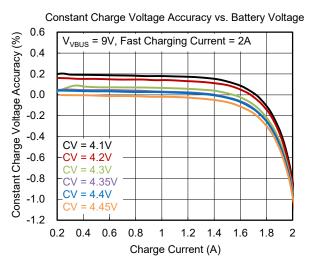
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V <sub>VBUS</sub> /V <sub>BAT</sub> Power-Up						
VBUS OVP Reaction Time	t <sub>ACOV</sub>	V <sub>VBUS</sub> rising above ACOV threshold to turn off Q2		100		ns
Wait Window for Bad Adapter Detection	t <sub>BAD_SRC</sub>			42		ms
Battery Charger						
Deglitch Time for Charge Termination	t <sub>TERM_DGL</sub>			168		ms
Deglitch Time for Recharge	t <sub>RECHG_DGL</sub>			168		ms
Battery Over-Voltage Deglitch Time to Disable Charge	t <sub>BATOVP</sub>			1		μs

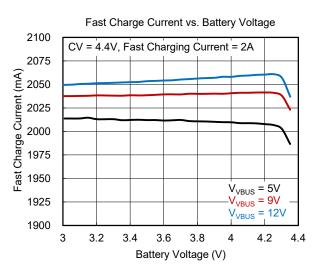
### TYPICAL PERFORMANCE CHARACTERISTICS

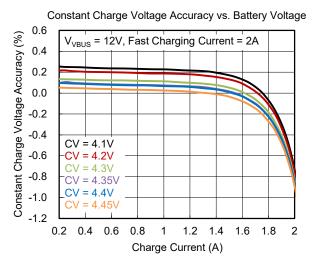




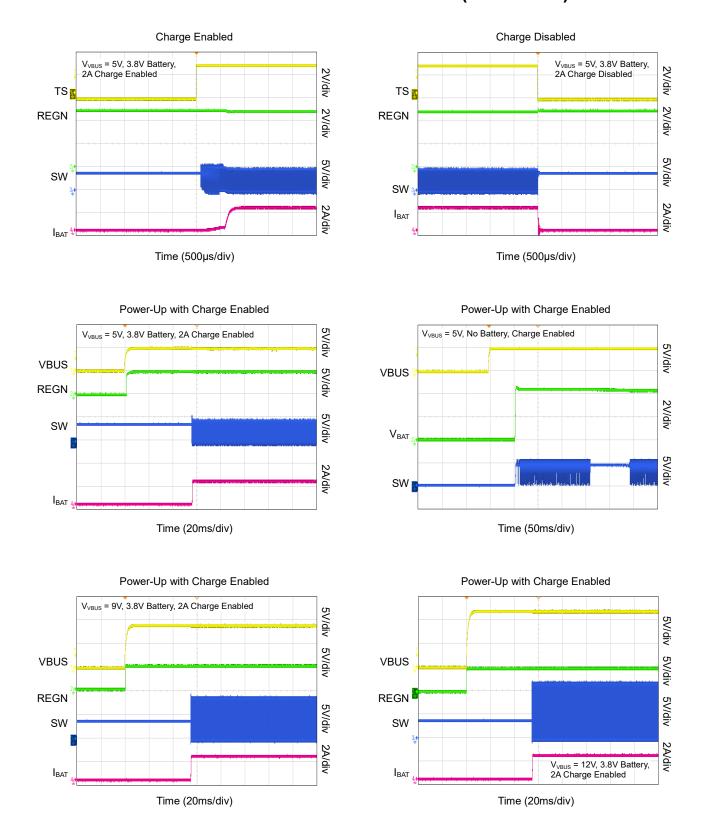








## **TYPICAL PERFORMANCE CHARACTERISTICS (continued)**



### TYPICAL APPLICATION CIRCUIT

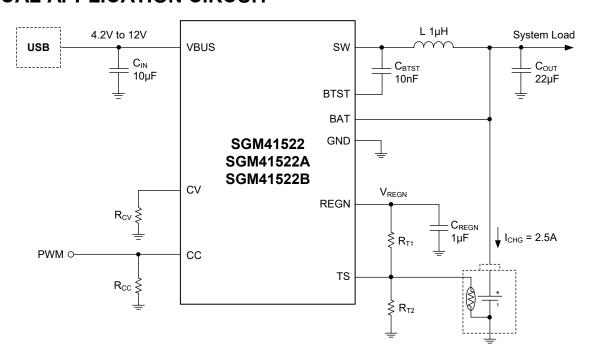


Figure 1. Typical Application Circuit

### **FUNCTIONAL BLOCK DIAGRAM**

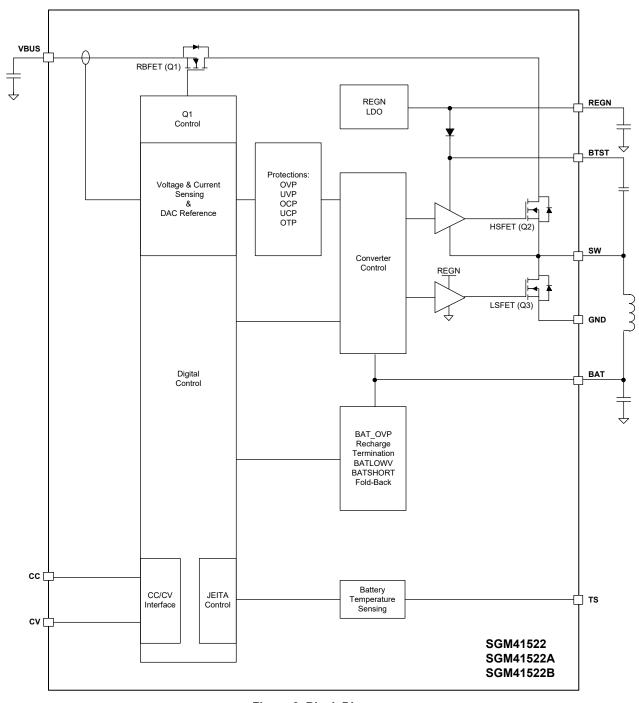


Figure 2. Block Diagram

### **DETAILED DESCRIPTION**

#### Overview

The SGM41522, SGM41522A and SGM41522B are highly-integrated 2.5A switch-mode stand-alone battery charge management devices for applications such as cell phones, tablets and portable devices that use single-cell Li-lon and Li-polymer batteries. The devices have a low impedance power path that improves the operation efficiency of the switch-mode, reduces the battery charging time and extends battery life in the discharging phase. The charging setting with the CC/CV interface makes the device a flexible solution. These devices include three main power switches: input reverse blocking FET (RBFET, Q1), high-side switching FET (HSFET, Q2) and low-side switching FET (LSFET, Q3). The bootstrap diode of the high-side gate drive is also integrated to simplify the system design.

The start and termination of a charging cycle can be accomplished without software control. The sensed battery voltage is used to decide the starting phase of charge in one of the three phases of charge cycle: pre-conditioning, constant current or constant voltage. When the charge current falls below a preset limit and the battery voltage is above recharge threshold, the charger function will automatically terminate and end the charging cycle. When the voltage of a charged battery is below the recharge threshold, the charger starts another charging cycle.

The SGM41522, SGM41522A and SGM41522B have several safety features, such as over-voltage and over-current protections, battery temperature monitoring, input UVLO and thermal shutdown. TS pin is connected to an NTC thermistor for battery temperature monitoring and protection in charge

mode according to JEITA profile. This device also features thermal regulation in which the charge current is reduced if the junction temperature exceeds 110°C.

#### Power-On Reset (POR)

The internal circuit of the device is powered from the voltage V<sub>VBUS</sub>. When the voltage of VBUS goes above its UVLO level (V<sub>VBUS</sub> > V<sub>VBUS\_UVLOZ</sub>), a POR happens and activates the sleep comparator. Upon activation, the CC/CV interface will also be ready for charge current and voltage settings.

#### **Battery Charging Management**

#### **Battery Charging Profile**

The SGM41522, SGM41522A and SGM41522B feature a full battery charging profile with five phases. In the beginning of the cycle, the battery voltage ( $V_{BAT}$ ) is tested and appropriate current and voltage regulation levels are selected as shown in Table 1. Depending on the detected status of the battery, the proper phase is selected to start or for continuation of the charging cycle. The phases are trickle charge ( $V_{BAT} < 2.19V$ ), pre-charge, fast-charge (constant current and constant voltage) and fold-back mode.

Table 1. Charge Current Setting Based on VBAT

V <sub>BAT</sub> Voltage	Charge Current
< 2.19V	I <sub>SHORT</sub>
2.19V to 3V	I <sub>PRECHG</sub>
> 3V	I <sub>CHGREG</sub>

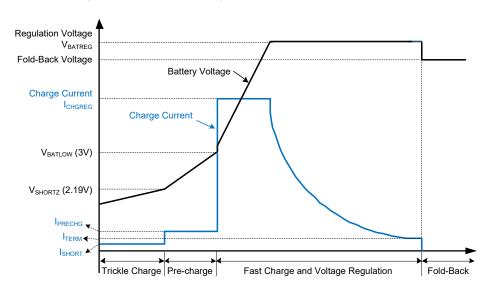


Figure 3. Battery Charging Profile



## **DETAILED DESCRIPTION (continued)**

#### **Charge Termination**

A charge cycle is terminated when the battery voltage is higher than the recharge threshold and the charge current falls below the programmed termination current. The termination current is programmed to I<sub>CHGREG</sub>/10 with a minimum clamped value of 50mA (TYP). To fully charge a battery, it is recommended to set the I<sub>CHGREG</sub> to be much higher than 50mA. After the charging cycle is completed, the converter enters fold-back mode.

The SGM41522, SGM41522A and SGM41522B have no battery switch but provide an alternative way for battery safe and extended battery life, which is the voltage fold-back mode when a battery is fully charged while the input power is kept. This alternative has less energy loss as no switch in the discharge loop. The only penalty is that it could not support instant start if the battery voltage is excessive low, in which condition it takes a few more minutes for the load system to be ready for start. When the device operates in FBM, the output voltage is  $V_{\text{FOLDBACK}}$  lower than  $V_{\text{BATREG}}$ , and the output current limit is  $I_{\text{CHGREG\_FOLDBACK}}$  (2.4A).

#### **Compliance with JEITA Guideline**

JEITA guideline (April 20, 2007 release) is implemented in the device for safe charging of the Li-lon battery. JEITA highlights the considerations and limits that should to be considered for charging at cold or hot battery temperatures. High charge current and voltage must be avoided outside normal operating temperatures (typically 0 °C and 60 °C). This functionality can be disabled if not needed. Four temperature levels are defined by JEITA from T1 (minimum) to T4 (maximum). Outside this range, charging should be stopped. The corresponding voltages sensed by NTC are named  $V_{T1}$  to  $V_{T4}$ . Due to the sensor negative resistance, a higher temperature results in a lower voltage on TS pin. The battery cool range is between T1 and T2, and the warm range is between T3 and T4. Charge must be limited in the cool and warm ranges.

One of the conditions for starting a charge cycle is having the TS voltage within  $V_{T1}$  to  $V_{T4}$  window limits. If during the charge, battery gets too cold or too hot and TS voltage exceeds the T1 - T4 limits, charging is suspended (zero charge current) and the controller waits for the battery temperature to come back within the T1 to T4 window.

At cool temperature (T1 - T2) or at warm temperature (T3 - T4), the charge current reduces to 10% of the charge current, and the charge voltage is decreased by about 100mV automatically. Particularly, the SGM41522B is charge prohibited at warm temperature.

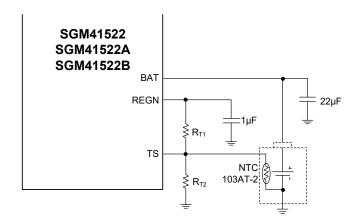


Figure 4. Battery Thermistor Connection and Bias Network

The resistor bias network (see Figure 4) can be calculated based on the following equations:

$$R_{T2} = \frac{R_{THCOLD} \times R_{THHOT} \times \left(\frac{1}{V_{T1}} - \frac{1}{V_{T4}}\right)}{R_{THHOT} \times \left(\frac{1}{V_{T4}} - 1\right) - R_{THCOLD} \times \left(\frac{1}{V_{T1}} - 1\right)}$$
(1)

$$R_{T1} = \frac{\left(\frac{1}{V_{T1}} - 1\right)}{\left(\frac{1}{R_{T2}}\right) + \left(\frac{1}{R_{THCOLD}}\right)}$$
(2)

where  $V_{T1}$  and  $V_{T4}$  are  $T_{COLD}$  and  $T_{HOT}$  threshold voltage on TS pin as percentage to  $V_{REGN}$ . Select  $T_{COLD}=0^{\circ}C$  and  $T_{HOT}=60^{\circ}C$  for Li-Ion or Li-polymer batteries. For a 103AT-2 type thermistor  $R_{THCOLD}=27.28k\Omega$  and  $R_{THHOT}=3.02k\Omega$ , the calculation results are:  $R_{T1}=5.18k\Omega$  and  $R_{T2}=29.34k\Omega$ . The standard value is  $5.23k\Omega$  for  $R_{T1}$  and  $29.4k\Omega$  for  $R_{T2}$ .

**Table 2. Temperature Related Charging Control** 

Temperature Range	Charge Current	Charge Voltage
Lower than T1	1	1
T1 - T2	I <sub>CHGREG</sub> × 10%	V <sub>BATREG</sub> - 100mV
T2 - T3	I <sub>CHGREG</sub>	$V_{BATREG}$
T3 - T4 (SGM41522/SGM41522A)	I <sub>CHGREG</sub> × 10%	V <sub>BATREG</sub> - 100mV
T3 - T4 (SGM41522B)	1	/
Higher than T4	1	1

## **DETAILED DESCRIPTION (continued)**

#### **Protections Features**

#### Input Over-Voltage

If VBUS voltage exceeds  $V_{VBUS\_OV}$ , switching will stop immediately. Charger resumes its normal operation when the voltage comes back below OVP limit.

#### Thermal Regulation and Thermal Shutdown

Internal junction temperature  $(T_J)$  is always monitored to avoid overheating. A limit of +110 °C is considered for maximum IC surface temperature in Buck mode and if  $T_J$  intends to exceed this level, the device reduces the charge current to keep maximum temperature limited to +110 °C (thermal regulation mode). As expected, the actual charging current is usually lower than programmed value during thermal regulation.

If the junction temperature exceeds  $T_{SHUT}$  (+150°C), thermal shutdown protection arises in which the converter is turned off

When the device recovers and  $T_J$  falls below the hysteresis band of  $T_{SHUT\_HYS}$  (10°C under  $T_{SHUT}$ ), the converter resumes automatically.

#### **Battery Over-Voltage Protection**

The over-voltage limit for the battery is 4.5% above the battery regulation voltage setting. Charging will immediately disable if a battery over-voltage occurs.

#### **Battery Over-Discharge Protection**

To recover from over-discharge, an input source is required at VBUS pin. The battery is charged with  $I_{SHORT}$  (33.5mA TYP) when the  $V_{BAT}$  <  $V_{SHORT}$ , or with a pre-charge current when the battery voltage is between  $V_{SHORT}$  and  $V_{BATLOW}$ .

#### **Charging Voltage Programming**

Forcing a voltage on the CV pin, or grounding it with a resistor that presents a similar voltage against the constant current sourcing from the pin during charging selects 1 of 6 charging voltages, as shown in Table 3.

#### **Charge Current Programming and Turn-Off**

Charge current is programmed by using different  $R_{\text{CC}}$  resistance or by providing voltage difference on the  $R_{\text{CC}}$  by forcing a voltage on the other end, which could be generated by a DAC or PWM output.

Forcing the CC to a voltage higher than  $V_{\text{CC\_H}}$  (1.4V) turns the device off.

Table 3. Conditions for Selecting a Charging Voltage

Charging Voltage (V)	Forcing Voltage (V)	Separation Thresholds (V)	Recommended Grounding Resistance ( $k\Omega$ )
4.1	0.45	0.3 ~ 0.6	9.09
4.2	Grounding or Open	< 0.3 or > 2.0	Grounding or Floating
4.3	0.75	0.6 ~ 0.9	15
4.35	1.05	0.9 ~ 1.2	21
4.4	1.4	1.2 ~ 1.6	28
4.45	1.8	1.6 ~ 2.0	35.7

NOTE: Sourcing current out of the CV is typically 50µA.

## **DETAILED DESCRIPTION (continued)**

#### **Layout Guide**

- 1. Place the input capacitor between VBUS and GND pins as close as possible to the chip with the shortest copper connections (avoid vias).
- 2. Connect one pin of the inductor as close as possible to the SW pin of the device and minimize the copper area connected to the SW node to reduce capacitive coupling from SW area to nearby signal traces. This decreases the noise induced through parasitic stray capacitances and displacement currents to other conductors. SW connection should be wide enough to carry the charging current. Keep other signals and traces away from SW if possible.
- 3. Place output capacitor GND pin as close as possible to the GND pin of the device and the GND pin of input capacitor  $C_{\text{IN}}$ . It is better to avoid using vias for these connections and keep the high frequency currents paths very short and on the same layer. A GND copper layer under the component layer helps reducing noise emissions.
- 4. Solder the exposed thermal pad of the package to the PCB ground planes. Ensure that there are enough thermal vias directly under the IC, connecting to the ground plane on the other layers for better heat dissipation and cooling of the device.

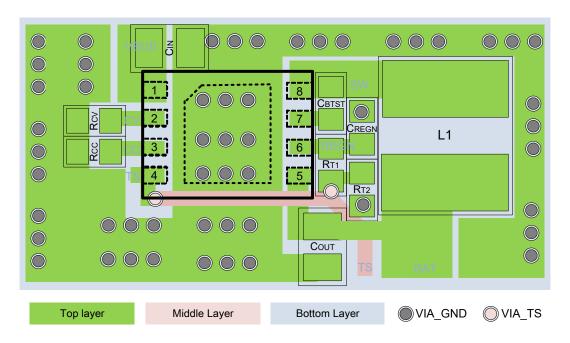


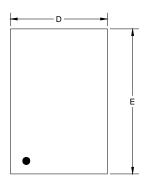
Figure 5. PCB Layout

### **REVISION HISTORY**

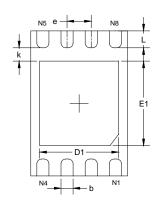
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

SEPTEMBER 2022 – REV.A.1 to REV.A.2	Page
Added part number SGM41522B	All
SEPTEMBER 2022 – REV.A to REV.A.1	Page
Updated Electrical Characteristics section	4, 5
Changes from Original (AUGUST 2022) to REV.A	Page
Changed from product preview to production data	All

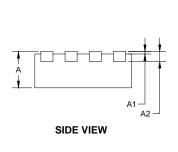
# PACKAGE OUTLINE DIMENSIONS TDFN-2×3-8BL

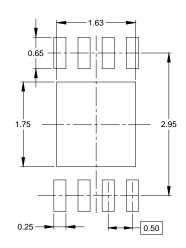


**TOP VIEW** 



**BOTTOM VIEW** 





RECOMMENDED LAND PATTERN (Unit: mm)

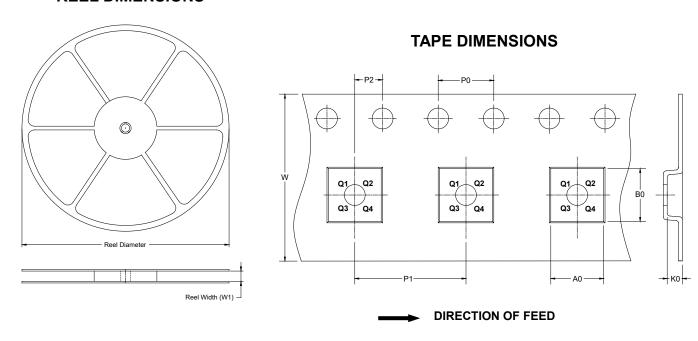
Symbol		nsions meters	Dimensions In Inches		
	MIN	MAX	MIN	MAX	
А	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A2	0.203	REF	0.008 REF		
D	1.950	2.050	0.077	0.081	
D1	1.530	1.730	0.060	0.068	
E	2.950	3.050	0.116	0.120	
E1	1.650	1.850	0.065	0.073	
b	0.200	0.300	0.008	0.012	
е	0.500 BSC		0.020 BSC		
k	0.250	REF	0.010 REF		
L	0.300	0.450	0.012	0.018	

NOTE: This drawing is subject to change without notice.



## TAPE AND REEL INFORMATION

#### **REEL DIMENSIONS**

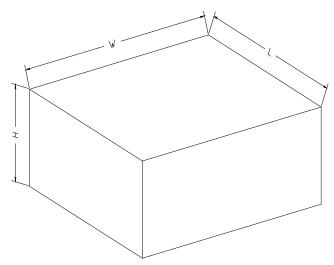


NOTE: The picture is only for reference. Please make the object as the standard.

#### **KEY PARAMETER LIST OF TAPE AND REEL**

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
TDFN-2×3-8BL	7"	9.5	2.30	3.30	1.10	4.0	4.0	2.0	8.0	Q2

#### **CARTON BOX DIMENSIONS**



NOTE: The picture is only for reference. Please make the object as the standard.

#### **KEY PARAMETER LIST OF CARTON BOX**

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
7" (Option)	368	227	224	8
7"	442	410	224	18